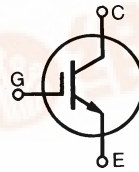




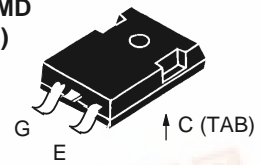
IXGH 32N60A  
IXGH 32N60AS

# HiPerFAST™ IGBT

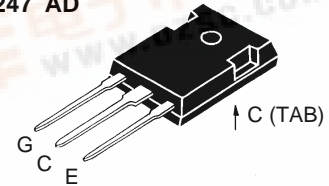
$V_{CES} = 600\text{ V}$   
 $I_{C25} = 60\text{ A}$   
 $V_{CE(sat)} = 2.9\text{ V}$   
 $t_{fi} = 125\text{ ns}$



TO-247 SMD  
(32N60AS)



TO-247 AD



G = Gate  
E = Emitter  
C = Collector  
TAB = Collector

Symbol	Test Conditions	Maximum Ratings	
$V_{CES}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
$V_{CGR}$	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1\text{ M}\Omega$	600	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ\text{C}$	60	A
$I_{C90}$	$T_C = 90^\circ\text{C}$	32	A
$I_{CM}$	$T_C = 25^\circ\text{C}, 1\text{ ms}$	120	A
<b>SSOA (RBSOA)</b>	$V_{GE} = 15\text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 33\ \Omega$ Clamped inductive load, $L = 100\ \mu\text{H}$	$I_{CM} = 64$ @ $0.8 V_{CES}$	A
$P_c$	$T_C = 25^\circ\text{C}$	200	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
$M_d$	Mounting torque (M3)	1.13/10Nm/lb.in.	
<b>Weight</b>		TO-247 AD	6 g
		TO-247 SMD	4 g

### Features

- International standard packages  
JEDEC TO-247 SMD surface mountable and JEDEC TO-247 AD
- High current handling capability
- 2nd generation HDMOS™ process
- MOS Gate turn-on - drive simplicity

### Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies

### Advantages

- Space savings (two devices in one package)
- High power density
- Suitable for surface mounting
- Switching speed for high frequency applications
- Easy to mount with 1 screw, TO-247 (isolated mounting screw hole)

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$BV_{CES}$	$I_C = 250\ \mu\text{A}, V_{GE} = 0\text{ V}$	600		V
$V_{GE(th)}$	$I_C = 250\ \mu\text{A}, V_{CE} = V_{GE}$	2.5		V
$I_{CES}$	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0\text{ V}$	$T_J = 25^\circ\text{C}$		200 $\mu\text{A}$
		$T_J = 125^\circ\text{C}$		1 mA
$I_{GES}$	$V_{CE} = 0\text{ V}, V_{GE} = \pm 20\text{ V}$			$\pm 100\text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}, V_{GE} = 15\text{ V}$			2.9 V



